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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	26
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/s9s08rna32w1mlcr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



- Input/Output
 - Up to 55 GPIOs including one output-only pin
 - Two 8-bit keyboard interrupt modules (KBI)
 - Two true open-drain output pins
 - Eight, ultra-high current sink pins supporting 20 mA source/sink current
- Package options
 - 64-pin LQFP
 - 48-pin LQFP
 - 32-pin LQFP



1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: RN60, RN48 and RN32.

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

S 9 S08 RN AA F1 B CC

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
s	Qualification status	S = fully qualified, general market flow
9	Memory	9 = flash based
S08	Core	• S08 = 8-bit CPU
RN	Device family	• RN
AA	Approximate flash size in KB	 60 = 60 KB 48 = 48 KB 32 = 32 KB
F1	Fab and mask set identifier	• W1
В	Temperature range (°C)	• M = -40 to 125



Field	Description	Values
CC	Package designator	 LH = 64-pin LQFP LF = 48-pin LQFP LC = 32-pin LQFP

2.4 Example

This is an example part number:

S9S08RN60W1MLH

3 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	- 55	150	°C	1
T _{SDR}	Solder temperature, lead-free	_	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.



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2. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	_	3	_	1

Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V _{HBM}	Electrostatic discharge voltage, human body model	-6000	+6000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I _{LAT}	Latch-up current at ambient temperature of 125°C	-100	+100	mA	

Determined according to JEDEC Standard JESD22-A114, Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM).

4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in below table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Symbol	Description	Min.	Max.	Unit
V_{DD}	Supply voltage	-0.3	5.8	V
I _{DD}	Maximum current into V _{DD}	_	120	mA

^{2.} Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.



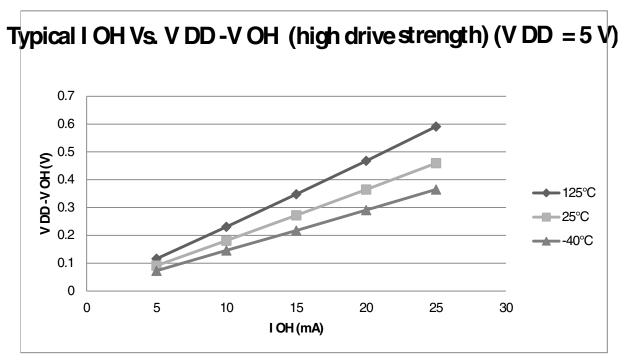


Figure 3. Typical I_{OH} Vs. V_{DD} - V_{OH} (high drive strength) (V_{DD} = 5 V)

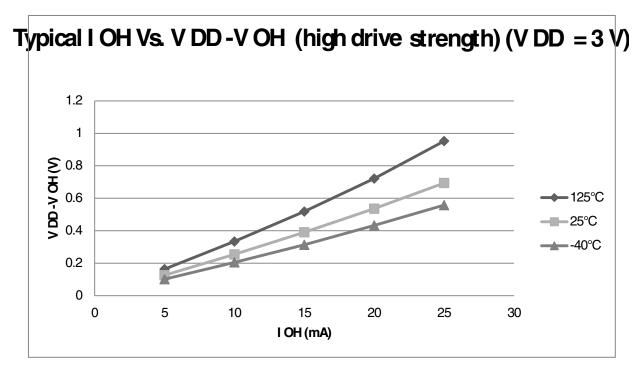


Figure 4. Typical I_{OH} Vs. V_{DD} - V_{OH} (high drive strength) (V_{DD} = 3 V)



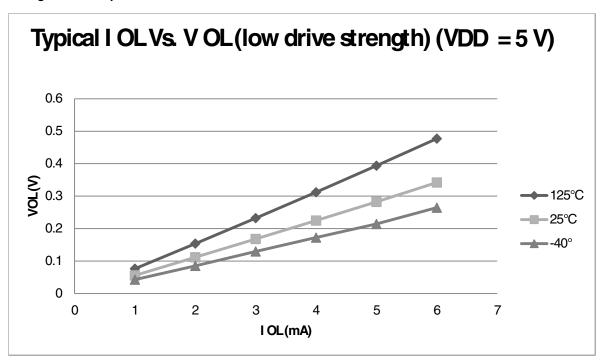


Figure 5. Typical I_{OL} Vs. V_{OL} (standard drive strength) ($V_{DD} = 5 \text{ V}$)

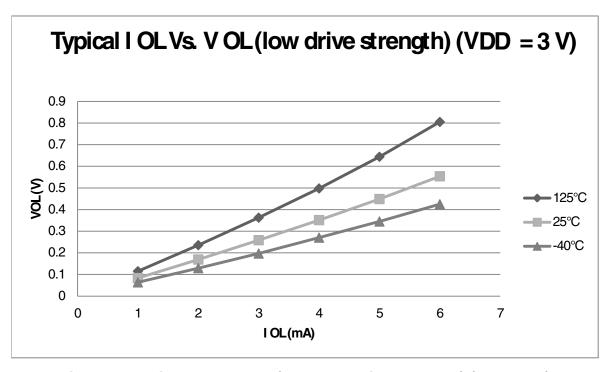


Figure 6. Typical I_{OL} Vs. V_{OL} (standard drive strength) ($V_{DD} = 3 \text{ V}$)



5.2 Switching specifications

5.2.1 Control timing

Table 5. Control timing

Num	С	Rating		Symbol	Min	Typical ¹	Max	Unit
1	Р	Bus frequency (t _{cyc} = 1/f _{Bus})		f _{Bus}	DC	_	20	MHz
2	Р	Internal low power oscillator	frequency	f _{LPO}	0.67	1.0	1.25	KHz
3	D	External reset pulse width ^{2,}	2	t _{extrst}	1.5 ×	_	_	ns
					t _{Self_reset}			
4	D	Reset low drive		t _{rstdrv}	$34 \times t_{cyc}$	_	_	ns
5	D	BKGD/MS setup time after debug force reset to enter u	t _{MSSU}	500	_	_	ns	
6	D	BKGD/MS hold time after is debug force reset to enter u	t _{MSH}	100	_	_	ns	
7	D	Keyboard interrupt pulse width			100	_	_	ns
	D		Synchronous path	t _{IHIL}	$1.5 \times t_{cyc}$	_	_	ns
8	С	Port rise and fall time -	_	t _{Rise}	_	10.2	_	ns
	С	Normal drive strength (HDRVE_PTXx = 0) (load = 50 pF) ^{4, 4}	E_PTXx = 0) (load		_	9.5	_	ns
	С	Port rise and fall time -	_	t _{Rise}	_	5.4	_	ns
	С	Extreme high drive strength (HDRVE_PTXx = 1) (load = 50 pF) ⁴		t _{Fall}	_	4.6	_	ns

- 1. Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.
- 2. This is the shortest pulse that is guaranteed to be recognized as a reset pin request.
- To enter BDM mode following a POR, BKGD/MS must be held low during the powerup and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.
- 4. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range -40 °C to 125 °C.

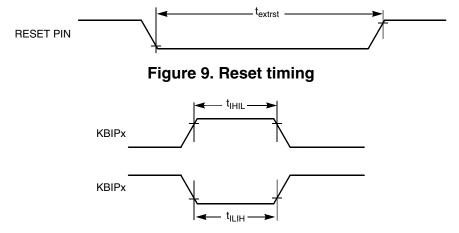


Figure 10. KBIPx timing

S9S08RN60 Series Data Sheet Data Sheet, Rev. 1, 01/2014.



5.2.2 Debug trace timing specifications

Table 6. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
t _{cyc}	Clock period	Frequency	MHz	
t _{wl}	Low pulse width	2	_	ns
t _{wh}	High pulse width	2	_	ns
t _r	Clock and data rise time	_	3	ns
t _f	Clock and data fall time	_	3	ns
t _s	Data setup	3	_	ns
t _h	Data hold	2	_	ns

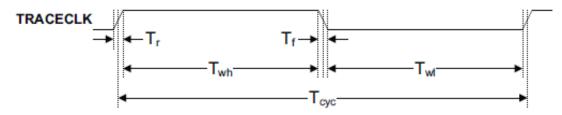


Figure 11. TRACE_CLKOUT specifications

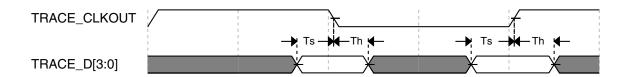


Figure 12. Trace data specifications

5.2.3 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 7. FTM input timing

No.	С	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f _{TCLK}	0	f _{Bus} /4	Hz

Table 7. FTM input timing (continued)

No.	С	Function	Symbol	Min	Max	Unit
2	D	External clock period	t _{TCLK}	4	_	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5	_	t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	_	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	_	t _{cyc}

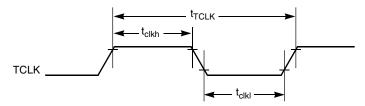


Figure 13. Timer external clock

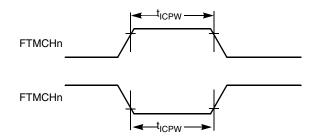


Figure 14. Timer input capture pulse

5.3 Thermal specifications

5.3.1 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.



Table 9. XOSC and ICS specifications (temperature range = -40 to 125 °C ambient) (continued)

Num	С	C	Characteristic	Symbol	Min	Typical ¹	Max	Unit
11	Р	Total deviation of DCO output from trimmed	Over full voltage range and temperature range of -40 to 125 °C	Δf_{dco_t}	_	_	±2.0	
	С	frequency ⁵	Over full voltage range and temperature range of -40 to 105 °C				±1.5	%f _{dco}
	С		Over fixed voltage and temperature range of 0 to 70 °C				±1.0	
12	С	FLL acquisition time ⁵ , ⁷		t _{Acquire}	_	_	2	ms
13	С	Long term jitter of DCO output clock (averaged over 2 ms interval) ⁸		C _{Jitter}	_	0.02	0.2	%f _{dco}

- 1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
- 2. When ICS is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.
- 3. See crystal or resonator manufacturer's recommendation.
- Load capacitors (C₁,C₂), feedback resistor (R_F) and series resistor (R_S) are incorporated internally when RANGE = HGO = 0.
- 5. This parameter is characterized and not tested on each device.
- 6. Proper PC board layout procedures must be followed to achieve specifications.
- 7. This specification applies to any time the FLL reference source or reference divider is changed, trim value changed, DMX32 bit is changed, DRS bit is changed, or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 8. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

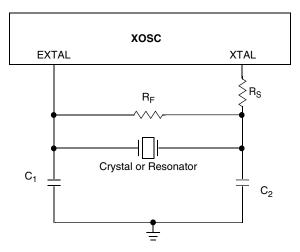


Figure 15. Typical crystal or resonator circuit



Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

6.3 Analog

6.3.1 ADC characteristics

Table 11. 5 V 12-bit ADC operating conditions

Characteri stic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
Supply	Absolute	V _{DDA}	2.7	_	5.5	V	_
voltage	Delta to V _{DD} (V _{DD} -V _{DDAD})	ΔV_{DDA}	-100	0	+100	mV	
Ground voltage	Delta to V _{SS} (V _{SS} -V _{SSA}) ²	ΔV_{SSA}	-100	0	+100	mV	
Input voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	
Input capacitance		C _{ADIN}	_	4.5	5.5	pF	
Input resistance		R _{ADIN}	_	3	5	kΩ	_
Analog source	12-bit mode • f _{ADCK} > 4 MHz	R _{AS}	_	_	2	kΩ	External to MCU
resistance	• f _{ADCK} < 4 MHz		_	_	5		
	10-bit modef_{ADCK} > 4 MHz		_	_	5		
	• f _{ADCK} < 4 MHz		_	_	10		
	8-bit mode		_	_	10	1	
	(all valid f _{ADCK})						
ADC	High speed (ADLPC=0)	f _{ADCK}	0.4	_	8.0	MHz	_
conversion clock frequency	Low power (ADLPC=1)		0.4	_	4.0		

^{1.} Typical values assume $V_{DDA} = 5.0 \text{ V}$, Temp = 25°C, $f_{ADCK} = 1.0 \text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.

^{2.} DC potential difference.



Table 12. 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Characteristic	Conditions	С	Symb	Min	Typ ¹	Max	Unit
ADC asynchronous clock source	High speed (ADLPC = 0)	Р	f _{ADACK}	2	3.3	5	MHz
	Low power (ADLPC = 1)			1.25	2	3.3	
Conversion time (including sample	Short sample (ADLSMP = 0)	Т	t _{ADC}	_	20	_	ADCK cycles
time)	Long sample (ADLSMP = 1)			_	40	_	
Sample time	Short sample (ADLSMP = 0)	Т	t _{ADS}	_	3.5	_	ADCK cycles
	Long sample (ADLSMP = 1)			_	23.5	_	
Total unadjusted	12-bit mode	Т	E _{TUE}	_	±5.0	_	LSB ^{3, 3}
Error ^{2, 2}	10-bit mode	Р		_	±1.5	±2.0	-
	8-bit mode	Р		_	±0.7	±1.0	
Differential Non-	12-bit mode	Т	DNL	_	±1.0	_	LSB ³
Linearity	10-bit mode ^{4, 4}	Р		_	±0.25	±0.5	
	8-bit mode ⁴	Р		_	±0.15	±0.25	_
Integral Non-Linearity	12-bit mode	Т	INL	_	±1.0	_	LSB ³
	10-bit mode	Т		_	±0.3	±0.5	
	8-bit mode	Т		_	±0.15	±0.25	
Zero-scale error ^{5, 5}	12-bit mode	С	E _{ZS}	_	±2.0	_	LSB ³
	10-bit mode	Р		_	±0.25	±1.0	
	8-bit mode	Р		_	±0.65	±1.0	
Full-scale error ⁶	12-bit mode	Т	E _{FS}	_	±2.5	_	LSB ³
	10-bit mode	Т		_	±0.5	±1.0	
	8-bit mode	Т		_	±0.5	±1.0	
Quantization error	≤12 bit modes	D	EQ	_	_	±0.5	LSB ³
Input leakage error ⁷	all modes	D	E _{IL}		I _{In} * R _{AS}		mV
Temp sensor slope	-40°C- 25°C	D	m	_	3.266	_	mV/°C
	25°C- 125°C			_	3.638	_	
Temp sensor voltage	25°C	D	V _{TEMP25}	_	1.396	_	V

^{1.} Typical values assume $V_{DDA} = 5.0 \text{ V}$, Temp = 25°C, $f_{ADCK} = 1.0 \text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.

^{2.} Includes quantization.

^{3.} $1 LSB = (V_{REFH} - V_{REFL})/2^N$

^{4.} Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes

^{5.} $V_{ADIN} = V_{SSA}$

^{6.} $V_{ADIN} = V_{DDA}$

^{7.} I_{In} = leakage current (refer to DC characteristics)



6.3.2 Analog comparator (ACMP) electricals

Table 13. Comparator electrical specifications

С	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	_	5.5	V
Т	Supply current (Operation mode)	I _{DDA}	_	10	20	μΑ
D	Analog input voltage	V _{AIN}	V _{SS} - 0.3	_	V_{DDA}	V
Р	Analog input offset voltage	V _{AIO}	_	_	40	mV
С	Analog comparator hysteresis (HYST=0)	V _H	_	15	20	mV
С	Analog comparator hysteresis (HYST=1)	V _H	_	20	30	mV
Т	Supply current (Off mode)	I _{DDAOFF}	_	60	_	nA
С	Propagation Delay	t _D	_	0.4	1	μs

6.4 Communication interfaces

6.4.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20% V_{DD} and 70% V_{DD} , unless noted, and 100 pF load on all SPI pins. All timing assumes slew rate control is disabled and high drive strength is enabled for SPI output pins.

Table 14. SPI master mode timing

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f _{op}	Frequency of operation	f _{Bus} /2048	f _{Bus} /2	Hz	f _{Bus} is the bus clock
2	t _{SPSCK}	SPSCK period	2 x t _{Bus}	2048 x t _{Bus}	ns	$t_{Bus} = 1/f_{Bus}$
3	t _{Lead}	Enable lead time	1/2	_	t _{SPSCK}	_
4	t _{Lag}	Enable lag time	1/2	_	t _{SPSCK}	_
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{Bus} - 30	1024 x t _{Bus}	ns	_
6	t _{SU}	Data setup time (inputs)	15	_	ns	_
7	t _{HI}	Data hold time (inputs)	0	_	ns	_
8	t _v	Data valid (after SPSCK edge)	_	25	ns	_
9	t _{HO}	Data hold time (outputs)	0	_	ns	_



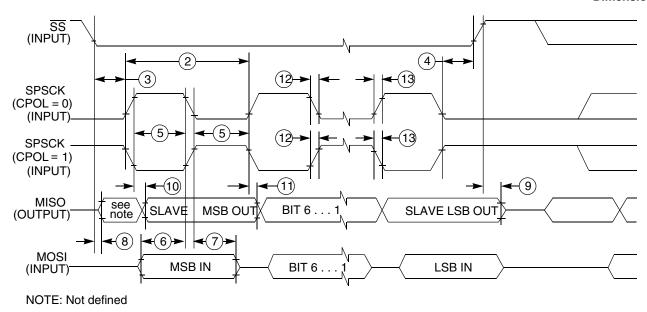


Figure 20. SPI slave mode timing (CPHA=1)

6.5 Human-machine interfaces (HMI)

6.5.1 TSI electrical specifications

Table 16. TSI electrical specifications

Symbol	Description	Min.	Туре	Max	Unit
TSI_RUNF	Fixed power consumption in run mode	_	100	_	μA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	_	128	μА
TSI_EN	Power consumption in enable mode	_	100	_	μA
TSI_DIS	Power consumption in disable mode	_	1.2	_	μA
TSI_TEN	TSI analog enable time	_	66	_	μs
TSI_CREF	TSI reference capacitor	_	1.0	_	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	-10	_	10	%

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

S9S08RN60 Series Data Sheet Data Sheet, Rev. 1, 01/2014.



Table 17. Pin availability by package pin-count (continued)

Pin Number			Lowest Priority <> Highest					
64-LQFP	48-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4	
20	16	11	PTC3	FTM2CH3	_	ADP11	_	
21	17	12	PTC2	FTM2CH2	_	ADP10	_	
22	18	_	PTD7	KBI1P7	TXD2	_	_	
23	19	_	PTD6	KBI1P6	RXD2	_	_	
24	20	_	PTD5	KBI1P5	_	_	_	
25	21	13	PTC1	_	FTM2CH1	ADP9	TSI7	
26	22	14	PTC0	_	FTM2CH0	ADP8	TSI6	
27	_	_	PTF7	_	_	ADP15	_	
28	_	_	PTF6	_	_	ADP14	_	
29	_	_	PTF5	_	_	ADP13	_	
30	_	_	PTF4	_	_	ADP12	_	
31	23	15	PTB3	KBI0P7	MOSI0	ADP7	TSI5	
32	24	16	PTB2	KBI0P6	SPSCK0	ADP6	TSI4	
33	25	17	PTB1	KBI0P5	TXD0	ADP5	TSI3	
34	26	18	PTB0	KBI0P4	RXD0	ADP4	TSI2	
35	_	_	PTF3	_	_	_	TSI15	
36	_	_	PTF2	_	_	_	TSI14	
37	27	19	PTA7	FTM2FAULT2	_	ADP3	TSI1	
38	28	20	PTA6	FTM2FAULT1	_	ADP2	TSI0	
39	29	_	PTE4	_	_	_	_	
40	30	_	_	_	_	_	V _{SS}	
41	31	_		_	_	_	V_{DD}	
42	_	_	PTF1	_	_	_	TSI13	
43	_	_	PTF0	_	_	_	TSI12	
44	32	_	PTD4	KBI1P4	_	_	_	
45	33	21	PTD3	KBI1P3	SS1	_	TSI11	
46	34	22	PTD2	KBI1P2	MISO1	_	TSI10	
47	35	23	PTA3 ^{2, 2}	KBI0P3	TXD0	SCL	_	
48	36	24	PTA2 ²	KBI0P2	RXD0	SDA	_	
49	37	25	PTA1	KBI0P1	FTM0CH1	ACMP1	ADP1	
50	38	26	PTA0	KBI0P0	FTM0CH0	ACMP0	ADP0	
51	39	27	PTC7	_	TxD1	_	TSI9	
52	40	28	PTC6		RxD1	_	TSI8	
53	41	_	PTE3	_	SS0	_	_	
54	42	_	PTE2	_	MISO0	_	_	
55	_	_	PTG3	_	_	_	_	
56	_	_	PTG2	_	_	_	_	
57	_	_	PTG1		_	_	_	



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Table 17. Pin availability by package pin-count (continued)

	Pin Number	1		Lowest F	Priority <> H	ighest	
64-LQFP	48-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
58	_	_	PTG0	_	_	_	_
59	43	_	PTE1 ¹	_	MOSI0	_	_
60	44	_	PTE0 ¹	_	SPSCK0	TCLK1	_
61	45	29	PTC5	_	FTM1CH1	_	_
62	46	30	PTC4	_	FTM1CH0	RTCO	_
63	47	31	_	_	_	_	RESET
64	48	32	_	_	_	BKGD	MS

- 1. This is a high current drive pin when operated as output.
- 2. This is a true open-drain pin when operated as output.

Note

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. The table above illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.



8.2 Device pin assignment

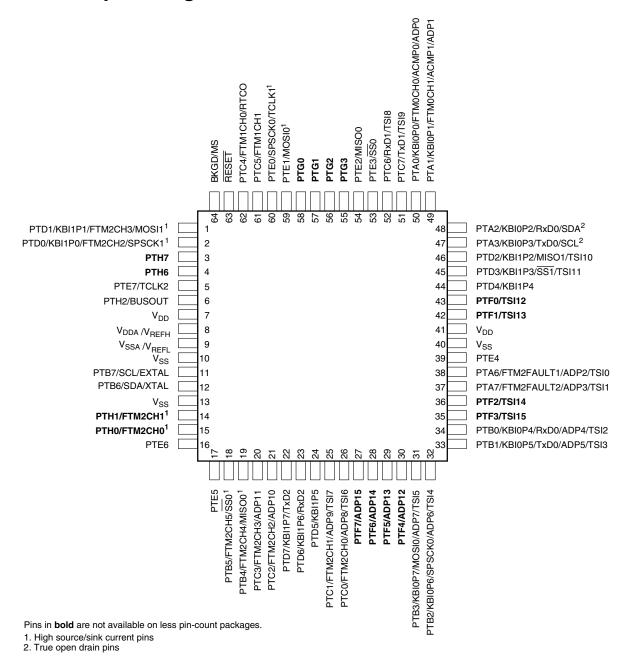


Figure 21. S9S08RN60 64-pin LQFP package

rmout

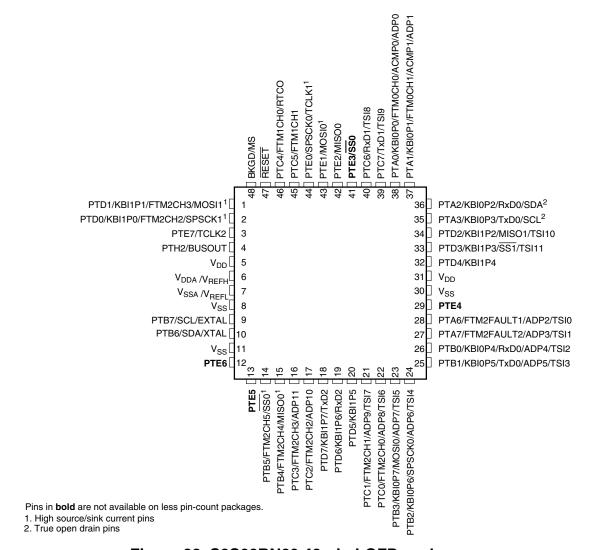


Figure 22. S9S08RN60 48-pin LQFP package



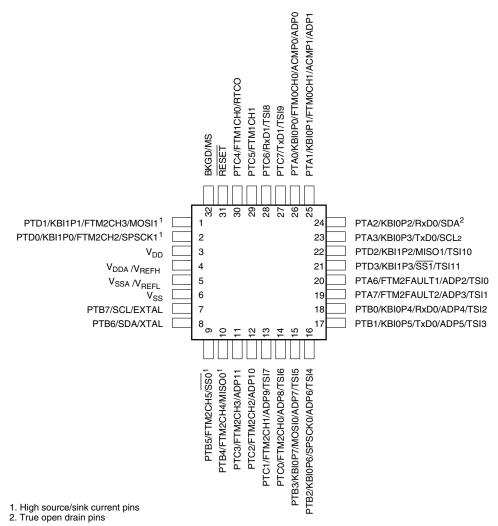


Figure 23. S9S08RN60 32-pin LQFP package

9 Revision history

The following table provides a revision history for this document.

Table 18. Revision history

Rev. No.	Date	Substantial Changes
1	01/2014	Initial Release



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